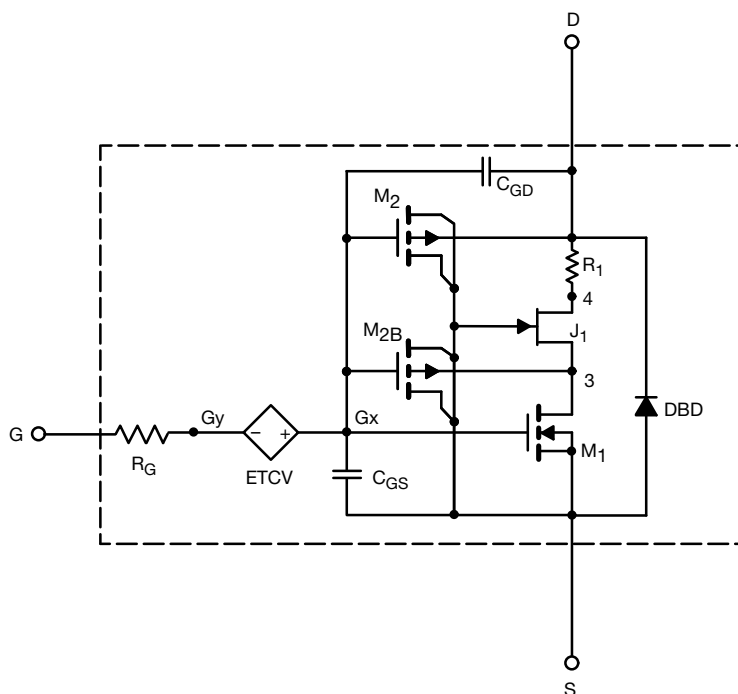# E Series Power MOSFET

DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over 25 °C to 150 °C temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over 25 °C to 150 °C temperature range
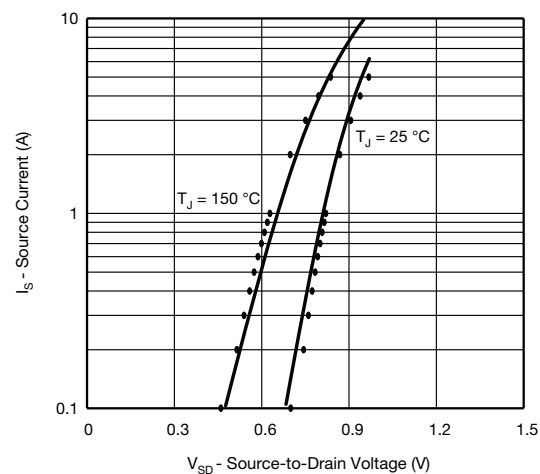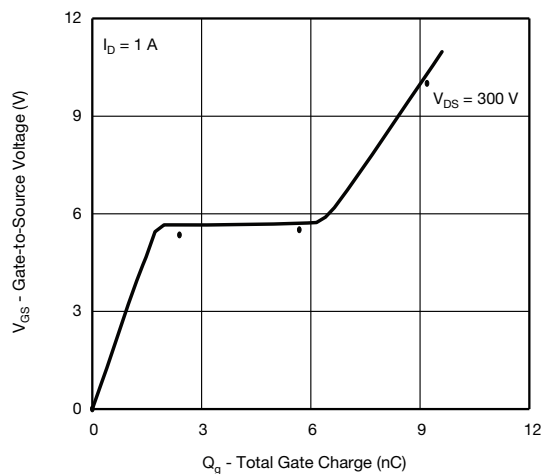- Model the gate charge

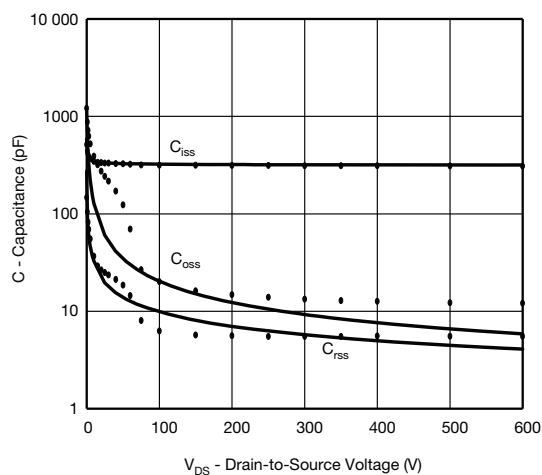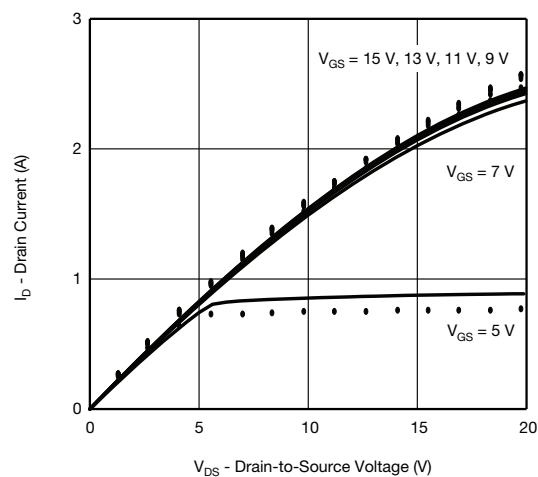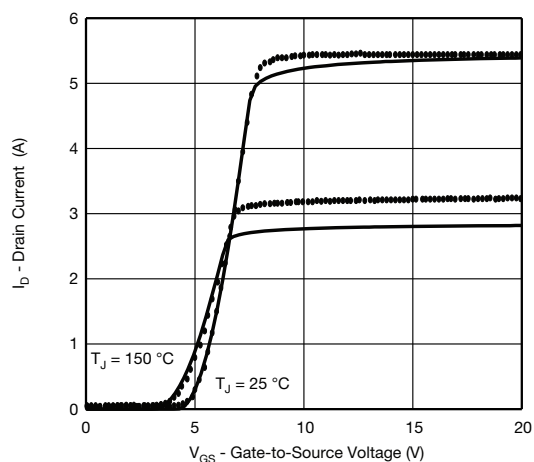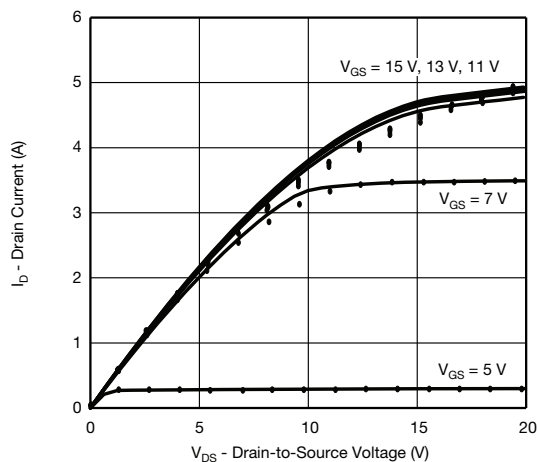## SUBCIRCUIT MODEL SCHEMATIC

Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	3	-	V
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 1 A	2.30	2.38	Ω
Forward transconductance	g_{fs}	V_{DS} = 30 V, I_D = 1 A	1.3	1	S
Dynamic					
Input capacitance	C_{iss}	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	324	315	pF
Output capacitance	C_{oss}		20	20	
Reverse transfer capacitance	C_{rss}		4.4	6	
Total gate charge	Q_g	V_{DS} = 480 V, V_{GS} = 10 V, I_D = 1 A	9.2	9.8	nC
Gate-source charge	Q_{gs}		1.8	2.4	
Gate-drain charge	Q_{gd}		4	3.9	
Drain-Source Body Diode Characteristics					
Reverse recovery time	t_{rr}	T_J = 25 °C, $I_F = I_S$ = 1 A, di/dt = 100 A/µs, V_R = 25 V	280	278	ns
Reverse recovery charge	Q_{rr}		2	0.9	µC

For technical questions, contact: hvm@vishay.com

COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)

Note

• Dots and squares represent measured data

Copyright: Vishay Intertechnology, Inc.